

# New Jersey Semi-Conductor Products, Inc.

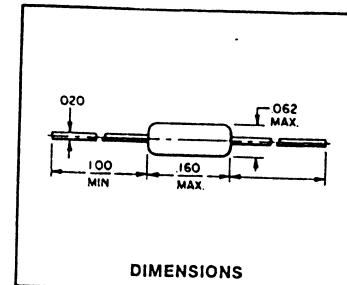
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1N5605 1N5606 1N5607 1N5608 1N5609®  
GENERAL PURPOSE DIODES

## GENERAL PURPOSE SILICON DIODES

This device is a Silicon Double Plug Diode for general purpose use in computer, industrial and military applications.



### ABSOLUTE MAXIMUM RATINGS

Storage temperature range, $T_{stg}$ .....	-65°C to +200°C		
Lead or terminal temperature at a distance not less than 1/16" from the seated surface (or case) for 15 seconds .....	+275°C		

	1N5605	1N5606	1N5607	1N5608/9
Reverse voltage, 25°C, free air .....	70 V	150 V	200 V	120 V
Maximum steady state power dissipation at 25°C, free air .....	250mw	200mw	200mw	250mw
Derating factor .....				2mw/°C

### ELECTRICAL CHARACTERISTICS

	1N5605		1N5606*	
	MIN	MAX	MIN	MAX
Forward Voltage, $V_f$ @ $I_f = 20$ ma .....	1.0 V		1.0 V	1.0 V
Breakdown Voltage, $B_v$ $I_r = 100$ ua .....	70 V		150 V	200 V
Reverse Current, $I_r$ @ $V_r = 60$ V .....	25 na		25 na	25 na
Reverse Current, $I_r$ @ $V_r = 60$ V @ 150°C .....	5 ua		5 ua	5 ua

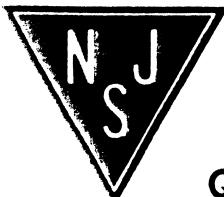
\*  $I_f = 7$  ma,  $V_r = 125$  V

\*  $I_f = 3$  ma,  $V_r = 175$  V

### 1N5605 1N5606 1N5607 1N5608

#### ELECTRICAL CHARACTERISTICS — 1N5608

	MIN	MAX
Forward Voltage, $V_f$ @ $I_f = 100$ ma .....		1.0 V
Breakdown Voltage, $B_v$ $I_r = 100$ ua .....		120 V
Reverse Current, $I_r$ @ 50 V .....		50 na
Reverse Current, $I_r$ @ 50 V @ 150°C .....		25 ua
*Reverse Recovery Time, $T_{rr}$ $I_f = 5$ ma, $V_r = 40$ V .....		300 nsec
$R_1 = 2$ K, $C_1 = 10$ pf .....		
Recover to 80K ohms .....		



Quality Semi-Conductors